

VERSION SHOWING THE CHANGES TO THE SPECIFICATION

IN THE SPECIFICATION:

Amend the specification as follows:

Paragraph [0014] of the published application:

Figure 1 shows a carrier substrate (for example a PET film) indicated at 1 with the corresponding lower conductor tracks 2 (for example gold, polyaniline, PEDOT, carbon black, graphite and conducting silver). The component comprises a plastic substrate which includes one of the following materials: PET, PP (~~polypropylene~~), PEN, polyimide, polyamide and coated paper.

Paragraph [00016] of the published application:

[00016] Figure 3 again shows the same structure in another stage in the process, where two further layers 4 and 5 which can comprise semiconducting or insulating material have already been applied over the through plating 3 of Fig. 2 and form fillets with the through plating comprising the upwardly inclined raised portions of each layer at their junctions with the through plating. See also Fig. 4. The following for example can be used as semiconductor: polyalkthiophene or polyfluorene, while the insulator used can be for example polyhydroxystyrene, ~~polymethacrylate~~ ~~polymethylmethacrylate~~ or polystyrene. By virtue of its size and/or its nature the through-plating 3 passes through the two central functional layers 4, 5 and thus forms the desired contact.

Paragraph [0022] of the published application:

[0022] The disruption element 7, Fig. 8, provides that, around it, the subsequently applied central functional layer 4 tears open (as manifested by the larger region of the layer 6 contiguous with the layer 2 next adjacent to the disruption element 7), Fig. 8) and/or, in the alternative, the layer 4 as shown in Figs. 5-7 (or layers 4 and 5) are absent, in the region of the through-plating 3. The conductor track 6 being is shown mounted directly on the layer 2, due to non-wetting or in some other fashion, by the presence of the non-wetting disruption element 7 on the layer 2, so that. Thus a region is produced around the disruption element 7, Fig. 8, (or as in Figs. 3-7, a comprising a void is created in the overlying layer(s), such as layer 4, due to the presence of the non-wetting disruption element 7 (e.g., the through-plating 3, or its equivalent), in which region the lower layer 2 to be contacted, as per Fig. 8, is exposed, in the operation of forming the upper layer conductor track 6 to be contacted.